CLAIMS

1. A polishing composition containing abrasive grains, a water-soluble polymer, an aggregation inhibitor, and water, the polishing composition being characterized in that, when an average particle size of the particles present in the polishing composition measured in accordance with a dynamic light scattering method is defined as R1 and an average particle size of the abrasive grains measured in accordance with a dynamic light scattering method in the case where the abrasive grains are dispersed in water so as to have the same concentration as the concentration of the abrasive grains in the polishing composition is defined as R2, R1/R2 is 1.3 or less,

wherein the water-soluble polymer is at least one selected from the group consisting of celluloses and polysaccharides, and

wherein the aggregation inhibitor is at least one selected from the group consisting of vinyl-based water-soluble polymers, oxyalkylene polymers, oxyalkylene copolymers, and silicone polymers

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2. The polishing composition according to claim 1, characterized in that the abrasive grains have an aspect ratio greater than 1 and not more than 4.0~~the water-soluble polymer is a cellulose~~.

3. The polishing composition according to claim 1 or 2, characterized in that the water-soluble polymer has a weight average molecular weight of 10,000 to 2,000,000.

4. The polishing composition according to any one of claims 1 to 3, characterized in that the aggregation inhibitor has a weight average molecular weight of 300 to 2,000,000.

5~~3~~. A method for polishing a silicon substrate, characterized by polishing a silicon substrate by using the polishing composition according to any one of claims 1 to 4~~claim 1 or 2~~.

6~~4~~. A method for producing a silicon substrate, characterized by polishing a silicon substrate by using the polishing method according to claim 5~~3~~.

CLAIMS

1. A polishing composition containing abrasive grains, a water-soluble polymer, an aggregation inhibitor, and water, the polishing composition being characterized in that, when an average particle size of the particles present in the polishing composition measured in accordance with a dynamic light scattering method is defined as R1 and an average particle size of the abrasive grains measured in accordance with a dynamic light scattering method in the case where the abrasive grains are dispersed in water so as to have the same concentration as the concentration of the abrasive grains in the polishing composition is defined as R2, R1/R2 is 1.3 or less,

wherein the water-soluble polymer is at least one selected from the group consisting of celluloses and polysaccharides, and

wherein the aggregation inhibitor is at least one selected from the group consisting of vinyl-based water-soluble polymers, oxyalkylene polymers, oxyalkylene copolymers, and silicone polymers.

2. The polishing composition according to claim 1, characterized in that the abrasive grains have an aspect ratio greater than 1 and not more than 4.0.

3. The polishing composition according to claim 1 or 2, characterized in that the water-soluble polymer has a weight average molecular weight of 10,000 to 2,000,000.

4. The polishing composition according to any one of claims 1 to 3, characterized in that the aggregation inhibitor has a weight average molecular weight of 300 to 2,000,000.

5. A method for polishing a silicon substrate, characterized by polishing a silicon substrate by using the polishing composition according to any one of claims 1 to 4.

6. A method for producing a silicon substrate, characterized by polishing a silicon substrate by using the polishing method according to claim 5.